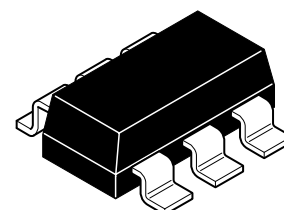


ZXMN2B03E6

20V SOT23-6 N-channel enhancement mode MOSFET with low gate drive capability

Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ (Ω)	I_D (A)
20	0.040 @ $V_{GS} = 4.5V$	5.4
	0.055 @ $V_{GS} = 2.5V$	4.6
	0.075 @ $V_{GS} = 1.8V$	4.0

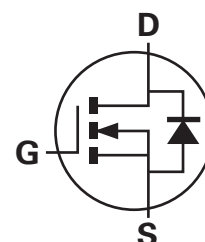


Description

This new generation trench MOSFET from Zetex features low on-resistance achievable with low gate drive.

Features

- Low on-resistance
- Fast switching speed
- Low gate drive capability
- SOT23-6 package

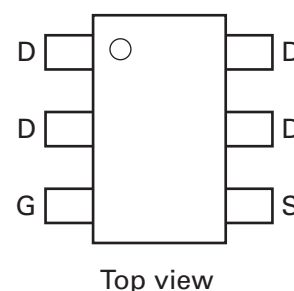


Applications

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN2B03E6TA	7	8	3,000



Device marking

2B3

ZXMN2B03E6

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{DSS}	20	V
Gate-source voltage	V_{GS}	± 8	V
Continuous drain current @ $V_{GS} = 4.5V$; $T_{amb}=25^{\circ}C^{(b)}$ @ $V_{GS} = 4.5V$; $T_{amb}=70^{\circ}C^{(b)}$ @ $V_{GS} = 4.5V$; $T_{amb}=25^{\circ}C^{(a)}$	I_D	5.4 4.3 4.3	A
Pulsed drain current ^(c)	I_{DM}	26	A
Continuous source current (body diode) ^(b)	I_S	2.8	A
Pulsed source current (body diode) ^(c)	I_{SM}	26	A
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$	P_D	1.1	W
Linear derating factor		8.8	mW/ $^{\circ}C$
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$	P_D	1.7	W
Linear derating factor		13.7	mW/ $^{\circ}C$
Operating and storage temperature range	T_J, T_{stg}	-55 to +150	$^{\circ}C$

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	113	$^{\circ}C/W$
Junction to ambient ^(b)	$R_{\theta JA}$	73	$^{\circ}C/W$

NOTES:

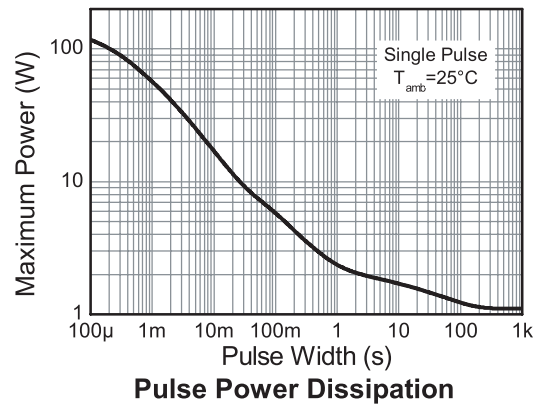
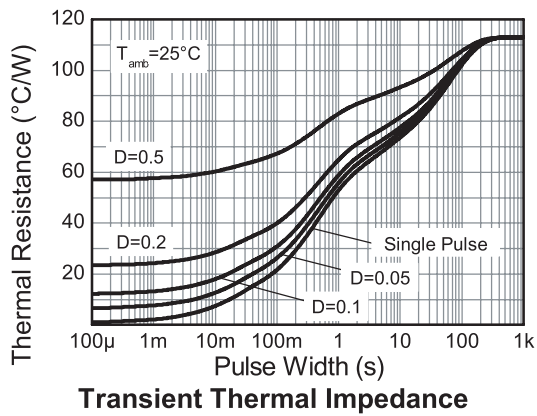
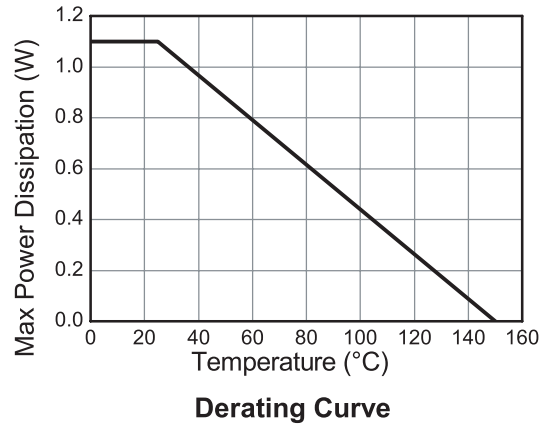
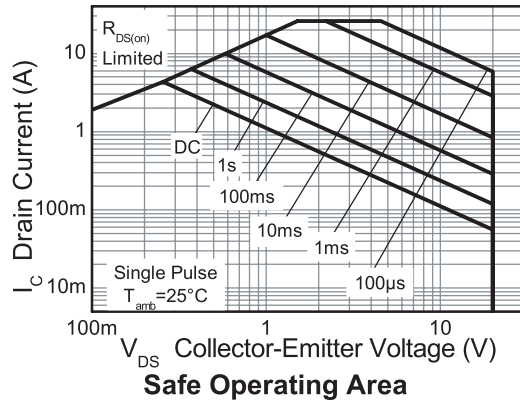
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ sec.

(c) Repetitive rating - 25mm x 25mm FR4 PCB, $D=0.02$, pulse width 300 μs - pulse width limited by maximum junction temperature.

ZXMN2B03E6

Thermal characteristics



ZXMN2B03E6

Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-source breakdown voltage	V _{(BR)DSS}	20			V	I _D = 250μA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}			1	μA	V _{DS} = 20V, V _{GS} =0V
Gate-body leakage	I _{GSS}			100	nA	V _{GS} =±8V, V _{DS} =0V
Gate-source threshold voltage	V _{GS(th)}	0.4		1.0	V	I _D = 250μA, V _{DS} =V _{GS}
Static drain-source on-state resistance ^(*)	R _{DS(on)}			0.040	Ω	V _{GS} = 4.5V, I _D = 4.3A
				0.055	Ω	V _{GS} = 2.5V, I _D = 3.7A
				0.075	Ω	V _{GS} = 1.8V, I _D = 3.2A
Forward transconductance ^(*) (‡)	g _{fs}		13.5		S	V _{DS} = 10V, I _D = 4.3A
Dynamic ^(‡)						
Input capacitance	C _{iss}		1160		pF	V _{DS} = 10V, V _{GS} =0V f=1MHz
Output capacitance	C _{oss}		210		pF	
Reverse transfer capacitance	C _{rss}		136		pF	
Switching ^(†) (‡)						
Turn-on-delay time	t _{d(on)}		4.2		ns	V _{DD} = 10V, V _{GS} = 4.5V I _D = 1A R _G ≈ 6.0Ω
Rise time	t _r		6.2		ns	
Turn-off delay time	t _{d(off)}		33.9		ns	
Fall time	t _f		12.4		ns	
Total gate charge	Q _g		14.5		nC	V _{DS} = 10V, V _{GS} = 4.5V I _D = 4.3A
Gate-source charge	Q _{gs}		2		nC	
Gate drain charge	Q _{gd}		2.8		nC	
Source-drain diode						
Diode forward voltage ^(*)	V _{SD}		0.67	0.95	V	T _j =25°C, I _S = 1.8A, V _{GS} =0V
Reverse recovery time ^(‡)	t _{rr}		10.8		ns	T _j =25°C, I _F = 2.8A, di/dt=100A/μs
Reverse recovery charge ^(‡)	Q _{rr}		3.4		nC	

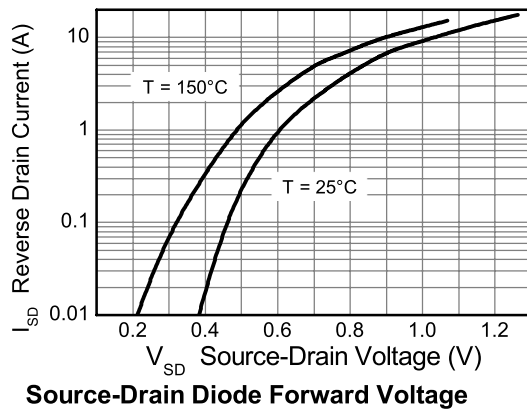
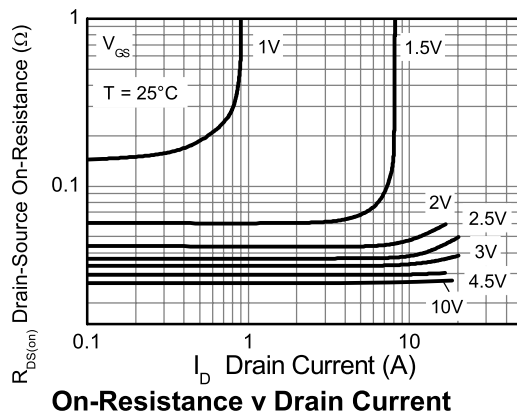
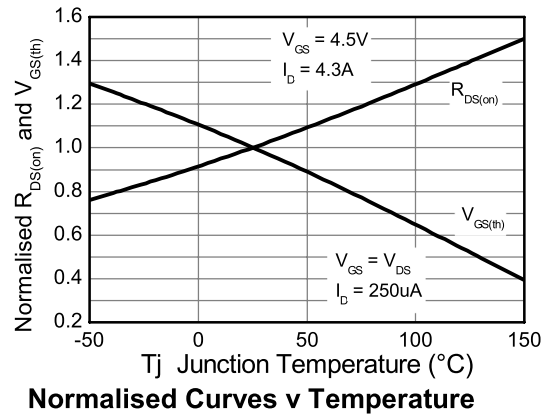
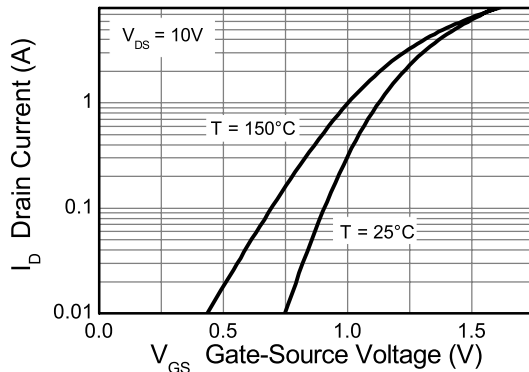
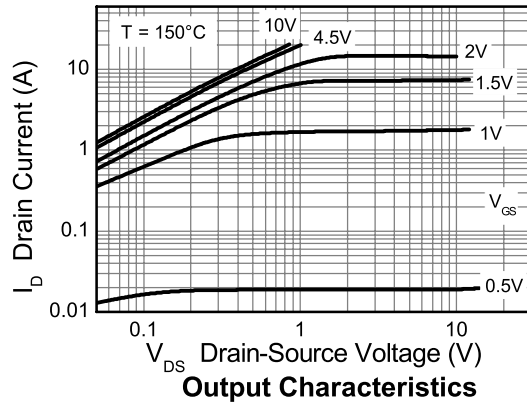
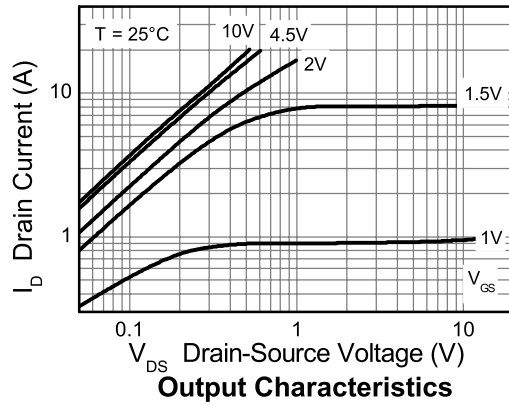
NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

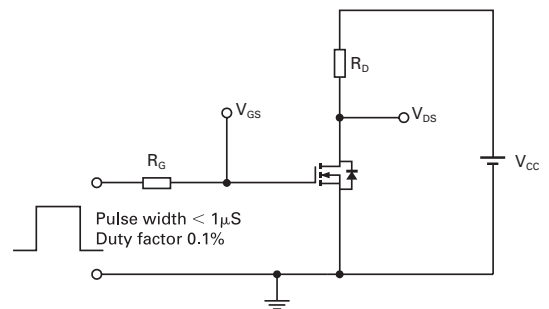
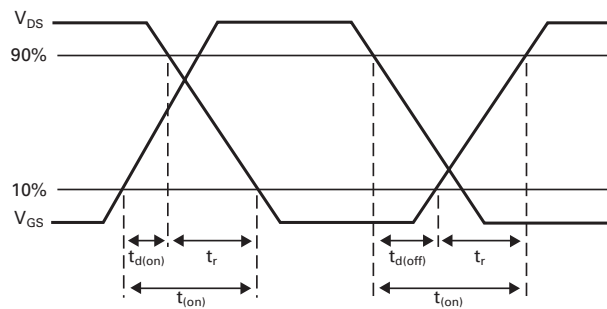
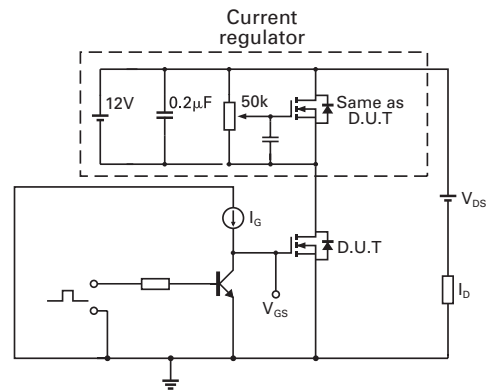
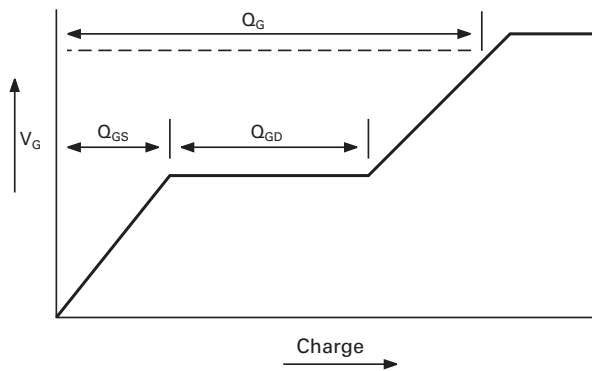
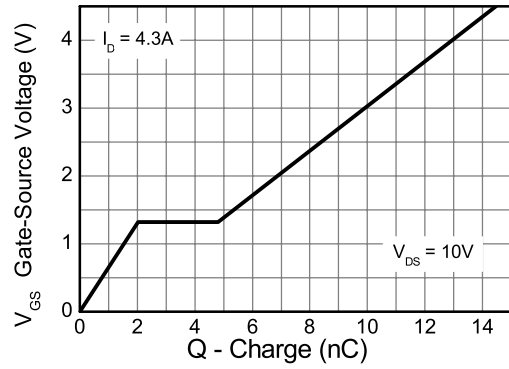
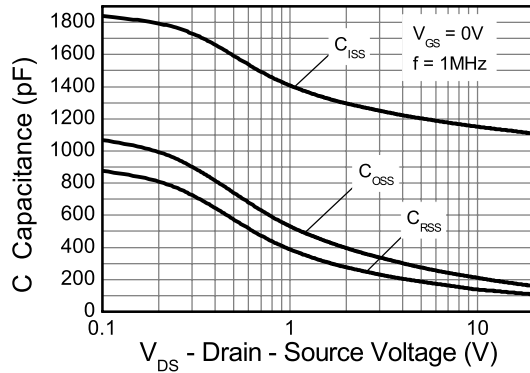
(†) Switching characteristics are independent of operating junction temperature.

(‡) For design aid only, not subject to production testing.

Typical characteristics



Typical characteristics

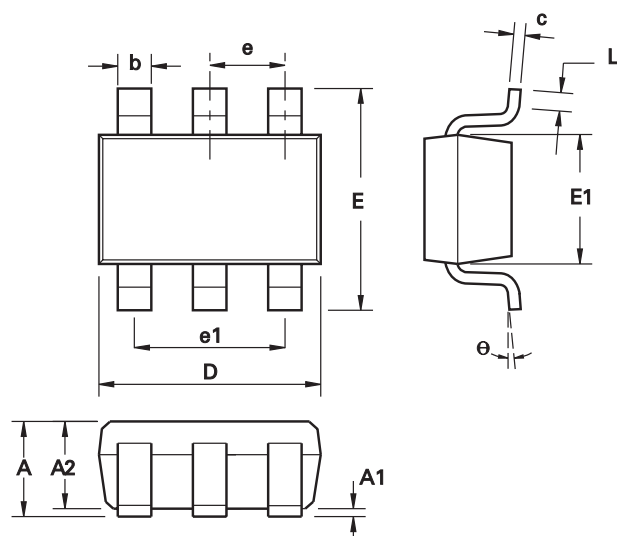


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Package outline - SOT23-6



DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.45	0.354	0.0570
A1	0.00	0.15	0.00	0.0059
A2	0.90	1.30	0.0354	0.0511
b	0.35	0.50	0.0078	0.0196
C	0.09	0.26	0.0035	0.0102
D	2.70	3.10	0.1062	0.1220
E	2.20	3.20	0.0866	0.1181
E1	1.30	1.80	0.0511	0.0708
L	0.10	0.60	0.0039	0.0236
e	0.95 REF		0.0374 REF	
e1	1.90 REF		0.0748 REF	
L	0°	30°	0°	30°

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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